

SAMSUNG SEMICONDUCTOR INC

14E D

7964142 0007249 7

**MMBC1623L5**

**NPN EPITAXIAL SILICON TRANSISTOR**

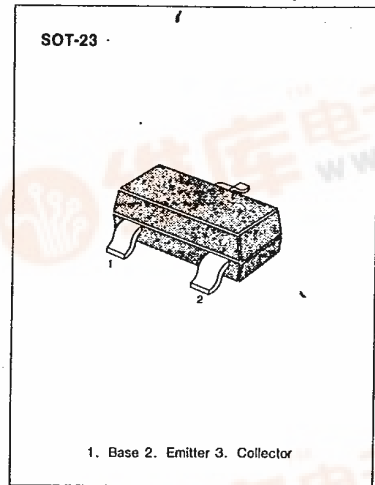
T-29-19

**AMPLIFIER TRANSISTOR**

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	50	V
Collector-Emitter Voltage	V <sub>CE0</sub>	40	V
Emitter-Base Voltage	V <sub>EB0</sub>	5.0	V
Collector Current	I <sub>c</sub>	100	mA
Collector Dissipation	P <sub>c</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C

• Refer to MMBC1623L3 for graphs



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0		100	nA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0		100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 6V, I <sub>C</sub> = 1.0mA	135	270	
Collector-Emitter Saturation Voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA		0.3	V
Base-Emitter Saturation Voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA		1.0	V
Base-Emitter On Voltage	V <sub>BE (on)</sub>	I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 6V	0.6	0.7	V
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 6V, I <sub>E</sub> = 10mA f = 100MHz	200		MHz

3

Marking

